Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8144	(porous or amorphous) near5 (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:31
L2	1800	(porous or amorphous) near5 (semiconductor adj layer) near5 (insulating or dielectric or insulator or oxide or passivation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:31
L3	15	((porous or amorphous) near5 (semiconductor adj layer) near5 (insulating or dielectric or insulator or oxide or passivation)) with (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:31
L4	10	((porous or amorphous) near5 (semiconductor adj layer) near5 (insulating or dielectric or insulator or oxide or passivation)) with (active adj matrix) with (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:34
L5	1	((porous or amorphous) near5 (semiconductor adj layer) near5 (insulating or dielectric or insulator or oxide or passivation)) with (active adj matrix) with (tft or (thin adj film adj transistor)) and radius	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:35
L6	35	((porous or amorphous) near5 (semiconductor adj layer) near5 (insulating or dielectric or insulator or oxide or passivation)) and (active adj matrix) with (tft or (thin adj film adj transistor)) and radius	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:35
L7	36	((porous or amorphous) near5 (semiconductor adj layer) near5 (insulating or dielectric or insulator or oxide or passivation)) and (active adj matrix) and (tft or (thin adj film adj transistor)) and radius	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:35
L8	1	((porous or amorphous) near5 (semiconductor adj layer) near5 (insulating or dielectric or insulator or oxide or passivation)) and (active adj matrix) and (tft or (thin adj film adj transistor)) and (radius near5 (pore or void or hole or porosity or porous))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:36

L9	8144	(porous or amorphous) near5 (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:36
L10	8253	(porous or amorphous or void) near5 (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:37
L11	8272	(porous or amorphous or void or pore) near5 (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:37
L12	15	(porous or amorphous or void or pore) near5 (semiconductor adj layer) and ((porous or amorphous or void or pore) near5 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:41
L13	24644	(active adj matrix) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:41
L14	20	(active adj matrix) and (tft or (thin adj film adj transistor)) and (radius near5 (void or hole or pore or porosity or porous))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:43
L15	459	(radius near5 void)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:43
L16	28	(radius near5 void) and ((amorphous or porous) near5 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:44
L17	2	(radius near5 void) with ((amorphous or porous) near5 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:45
L18	2	(radius near5 void) same ((amorphous or porous) near5 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:45

L19	36	(radius near5 (pore or void)) same ((amorphous or porous) near5 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:45
L20	14	(radius near5 (pore or void)) with ((amorphous or porous) near5 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:48
L21	1	(radius near5 (pore or void)) with ((amorphous or porous) near5 (silicon or semiconductor)) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:48
L22	13	(radius near5 (pore or void)) with ((amorphous or porous) near2 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:49
L23	10	(radius near5 (pore or void)) near10 ((amorphous or porous) near2 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:50
L24	10	(radius near2 (pore or void)) near10 ((amorphous or porous) near2 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:50
L25	13	(radius near2 (pore or void)) with ((amorphous or porous) near2 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:51
L26	15	(radius near2 (pore or void or hole)) with ((amorphous or porous) near2 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:51
L27	15	(radius near3 (pore or void or hole)) with ((amorphous or porous) near2 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:51
L28	17	(radius near3 (pore or void or hole)) with ((amorphous or porous) near5 (silicon or semiconductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:52

L29	14793	(semiconductor adj layer) with (amorphous or porous or void or hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:52
L30	5	(semiconductor adj layer) with (amorphous or porous or void or hole) with radius	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:54
L31	9	(semiconductor adj layer) same (amorphous or porous or void or hole) with radius	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:54
L32	38	(semiconductor adj layer) same (amorphous or porous or void or hole) same radius	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 10:55
L33	4	((semiconductor adj layer) same (amorphous or porous or void or hole) same radius).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:24
L34	161	(active adj matrix) same (tft or (thin adj film adj transistor)) same (semiconductor adj layer) same (amorpous or porous or hole or void) same electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:26
L35	8	((active adj matrix) same (tft or (thin adj film adj transistor)) same (semiconductor adj layer) same (amorpous or porous or hole or void) same electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:27
L36	1	((active adj matrix) same (tft or (thin adj film adj transistor)) same (semiconductor adj layer) same (amorpous or porous or pore or void) same electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:27
L37	2	((active adj matrix) same (tft or (thin adj film adj transistor)) same (semiconductor adj layer) same (amorpous or porous or pore or void) same electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:27
L38	2	((active adj matrix) same (tft or (thin adj film adj transistor)) same (semiconductor adj layer) same (amorpous or porous or pore or void))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:27

L39	252	((active adj matrix) same (tft or (thin adj film adj transistor)) same (semiconductor adj layer) same (amorphous or porous or pore or void))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:27
L40	13	((active adj matrix) same (tft or (thin adj film adj transistor)) same (semiconductor adj layer) same (amorphous or porous or pore or void) same electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:29
L41	11	((active adj matrix) with (tft or (thin adj film adj transistor)) same (semiconductor adj layer) same (amorphous or porous or pore or void) same electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:29
L42	11	((active adj matrix) with (tft or (thin adj film adj transistor)) with (semiconductor adj layer) same (amorphous or porous or pore or void) same electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:29
L43	5	((active adj matrix) with (tft or (thin adj film adj transistor)) with (semiconductor adj layer) with (amorphous or porous or pore or void) same electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:29
L44	5	((active adj matrix) with (tft or (thin adj film adj transistor)) with (semiconductor adj layer) with (amorphous or porous or pore or void) with electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:29

L59	0	I58 and ((amorphous near silicon near semiconductor near layer) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:38
L60	0	I58 and (((porous or amorphous) near2 silicon near2 semiconductor near layer) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:38
L61	0	(((porous or amorphous) near2 silicon near2 semiconductor near layer) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:38
L62	1	(((porous or amorphous) near2 semiconductor near layer) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:39
L63	1	(((porous or amorphous) near3 semiconductor near layer) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:39
L64	1456	(((porous or amorphous) "near5." semiconductor near layer) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:39
L65	1	(((porous or amorphous) near5 semiconductor near layer) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:39
L66	1	(((porous or amorphous) near5 (semiconductor near layer)) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:40
L67	1	(((porous or amorphous) near10 (semiconductor near layer)) near10 radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:40
L68	3	(((porous or amorphous) near10 (semiconductor near layer)) with radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:40

L69	192	((semiconductor near layer) with radius)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:40
L70	2	((semiconductor near layer) with ((pore or void) near5 radius))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:42
L71	627	((semiconductor near layer) with (pore or void))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:42
L72	96	((semiconductor near layer) with (pore or void)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:42
L73	70	((semiconductor near layer) near10 (pore or void)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:43
L74	24	((semiconductor near layer) near10 (pore or void)).clm. and ((diameter or radius) near10 (pore or void))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:43
L75	8	((semiconductor near layer) near10 (pore or void)).clm. and ((diameter or radius) near10 (pore or void)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 11:44